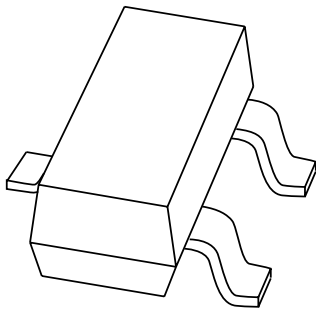


# DATA SHEET



**PBSS5120T**

20 V, 1 A

PNP low  $V_{CEsat}$  (BISS) transistor

Product specification

2003 Sep 29

## 20 V, 1 A PNP low $V_{CEsat}$ (BISS) transistor

### PBSS5120T

#### FEATURES

- Low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability  $I_C$  and  $I_{CM}$
- High efficiency leading to less heat generation
- Reduced printed-circuit board requirements
- Cost effective alternative for MOSFETs in specific applications.

#### APPLICATIONS

- Power management
  - DC/DC conversion
  - Supply line switching
  - Battery charger
  - LCD backlighting.
- Peripheral drivers
  - Driver in low supply voltage applications (e.g. lamps and LEDs)
  - Inductive load drivers (e.g. relays, buzzers and motors).

#### DESCRIPTION

PNP BISS transistor in a SOT23 plastic package providing ultra low  $V_{CEsat}$  and  $R_{CEsat}$  parameters.  
NPN complement: PBSS4120T.

#### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PBSS5120T	*3K

#### Note

- \* = p: made in Hong Kong.  
\* = t: made in Malaysia.  
\* = W: made in China.

#### ORDERING INFORMATION

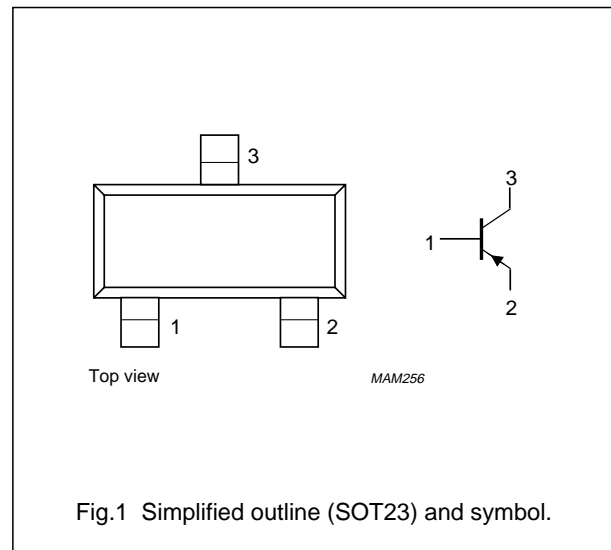
TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS5120T	–	plastic surface mounted package; 3 leads	SOT23

#### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	–20	V
$I_C$	collector current (DC)	–1	A
$I_{CM}$	peak collector current	–2	A
$R_{CEsat}$	equivalent on-resistance	250	m $\Omega$

#### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–20	V
$V_{CEO}$	collector-emitter voltage	open base	–	–20	V
$V_{EBO}$	emitter-base voltage	open collector	–	–5	V
$I_C$	collector current (DC)		–	–1	A
$I_{CM}$	peak collector current		–	–2	A
$I_{BM}$	peak base current		–	–200	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	300	mW
		$T_{amb} \leq 25\text{ °C}$ ; note 2	–	480	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C

**Notes**

1. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, standard footprint.
2. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	417	K/W
		in free air; note 2	260	K/W

**Notes**

1. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, standard footprint.
2. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.

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PBSS5120T

**CHARACTERISTICS** $T_{amb} = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector-base cut-off current	$V_{CB} = -20\text{ V}; I_E = 0$	–	–	–100	nA
		$V_{CB} = -20\text{ V}; I_E = 0; T_j = 150\text{ °C}$	–	–	–50	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = -4\text{ V}; I_C = 0$	–	–	–100	nA
$h_{FE}$	DC current gain	$V_{CE} = -2\text{ V}; I_C = -100\text{ mA}$	300	450	–	
		$V_{CE} = -2\text{ V}; I_C = -500\text{ mA}$	250	350	–	
		$V_{CE} = -2\text{ V}; I_C = -1\text{ A}$	200	290	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -100\text{ mA}; I_B = -1\text{ mA}$	–	–	–100	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	–	–125	mV
		$I_C = -1\text{ A}; I_B = -50\text{ mA}$	–	–	–250	mV
$R_{CEsat}$	equivalent on-resistance	$I_C = -500\text{ mA}; I_B = -50\text{ mA}; \text{note 1}$	–	–	250	$\text{m}\Omega$
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -2\text{ V}; I_C = -100\text{ mA}$	–	–	–0.75	V
$f_T$	transition frequency	$I_C = -100\text{ mA}; V_{CE} = -10\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
$C_C$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0; f = 1\text{ MHz}$	–	–	28	pF

**Note**

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

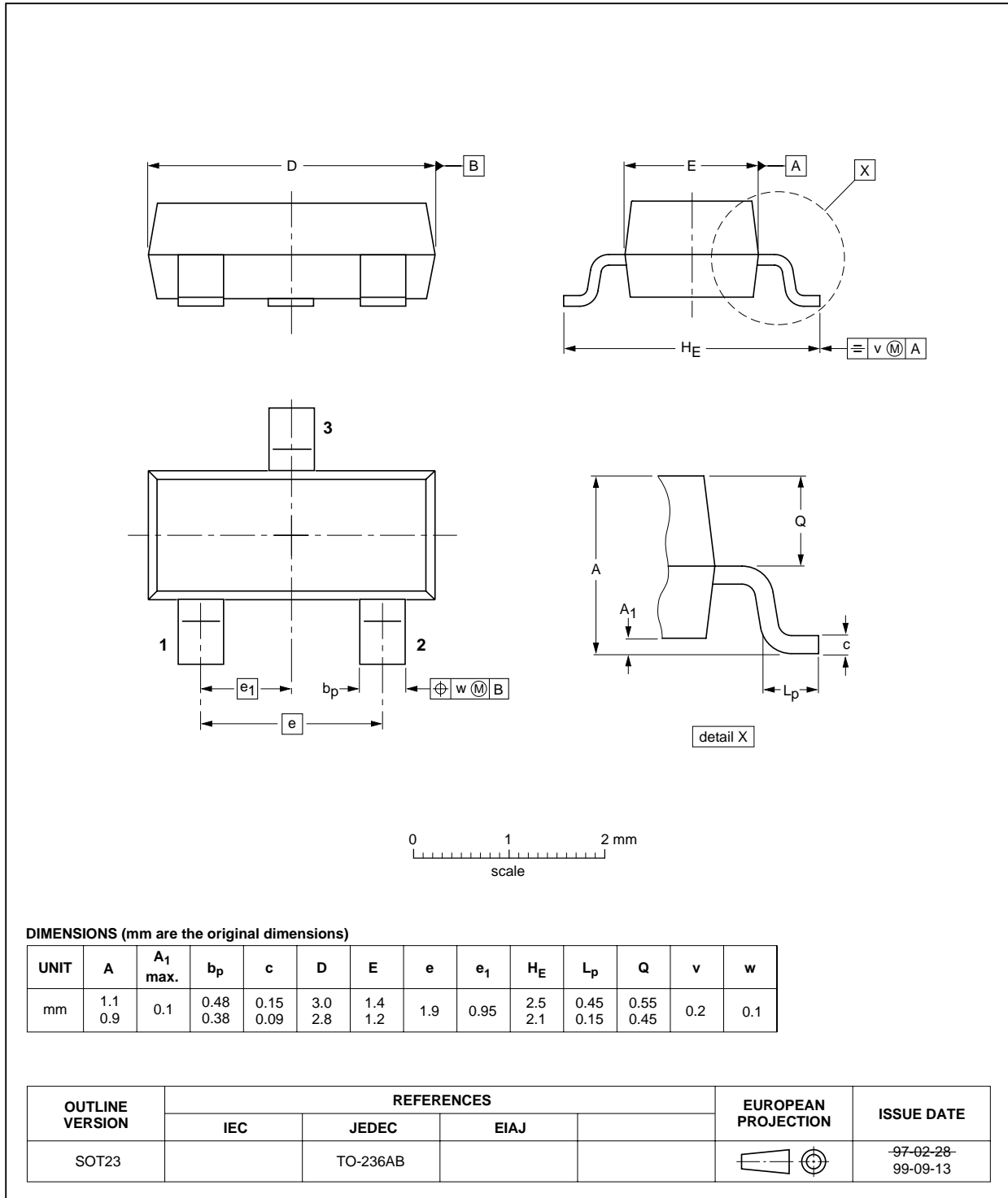
20 V, 1 A  
PNP low  $V_{CEsat}$  (BISS) transistor

PBSS5120T

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



20 V, 1 A  
PNP low  $V_{CEsat}$  (BISS) transistor

PBSS5120T

**DATA SHEET STATUS**

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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**Limiting values definition** — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device.

These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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